

NPN General Purpose Transistor

MMBTA05/MMBTA06

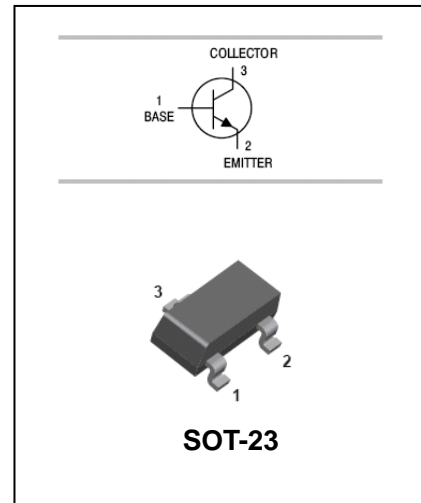
FEATURES

- Epitaxial planar die construction.
- Complementary PNP type available (MMBTA55/MMBTA56).
- Also available in lead free version.



APPLICATIONS

- Ideal for medium power amplification and switching



ORDERING INFORMATION

Type No.	Marking	Package Code
MMBTA05	1H	SOT-23
MMBTA06	1GM	SOT-23

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Symbol	Parameter	Value	UNIT
V _{CBO}	collector-base voltage	MMBTA05	60
		MMBTA06	80
V _{CEO}	collector-emitter voltage	MMBTA05	60
		MMBTA06	80
V _{EBO}	emitter-base voltage	4	V
I _C	collector current (DC)	0.5	A
P _C	Collector dissipation	0.35	W
R _{θJA}	Thermal Resistance, Junction to Ambient	357	°C/W
T _j , T _{stg}	junction and storage temperature	-55-150	°C

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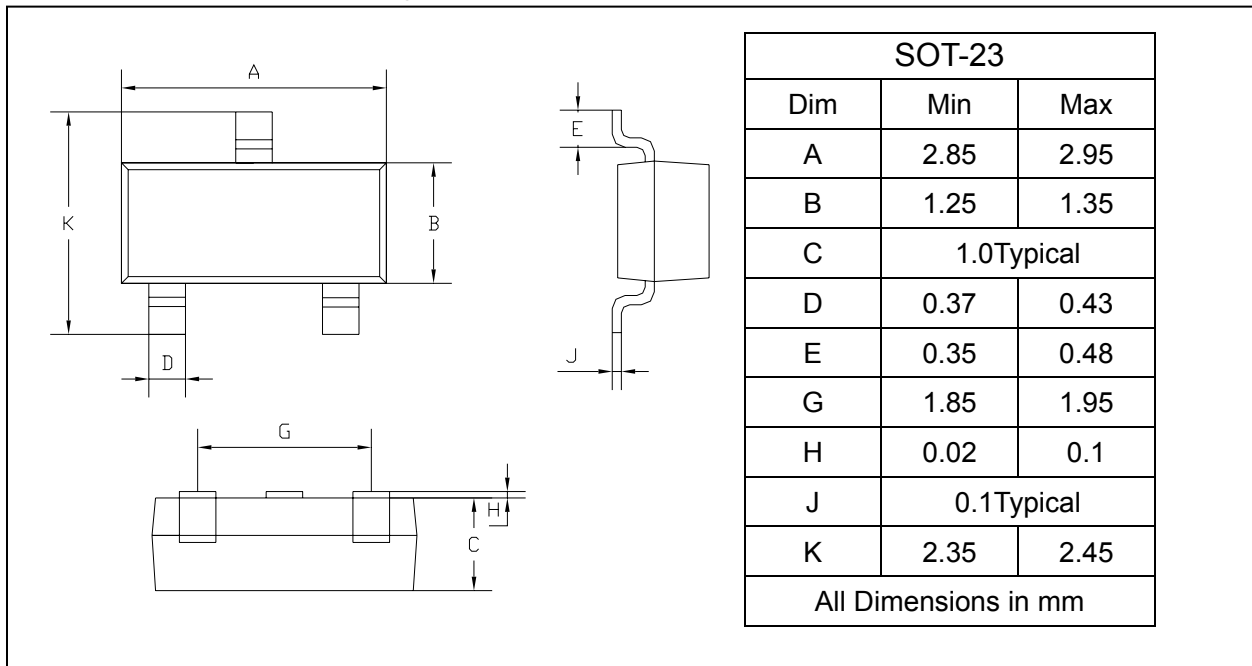
ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Symbol	Parameter	Test conditions	MIN.	MAX.	UNIT
$V_{(BR)CBO}$	Collector-base breakdown voltage MMBTA05 MMBTA06	$I_C=100\mu A, I_E=0$	60 80		V
$V_{(BR)CEO}$	Collector-emitter breakdown voltage MMBTA05 MMBTA06	$I_C=1.0mA, I_B=0$	60 80		V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=100\mu A, I_C=0$	4		V
I_{CBO}	collector cut-off current MMBTA05 MMBTA06	$I_E = 0; V_{CB} = 60V$ $I_E = 0; V_{CB} = 80V$	-	0.1	μA
I_{CEO}	collector cut-off current MMBTA05 MMBTA06	$I_E = 0; V_{CE} = 60V$ $I_E = 0; V_{CE} = 80V$	-	0.1	μA
h_{FE}	DC current gain	$V_{CE} = 1V; I_C = 10mA$ $V_{CE} = 1V; I_C = 100mA$	100	-	
$V_{CE(sat)}$	collector-emitter saturation voltage	$I_C = 100mA; I_B = 10mA$	-	0.25	V
f_T	transition frequency	$I_C = 10mA; V_{CE} = 2.0V;$ $f = 100MHz$	100	-	MHz

PACKAGE OUTLINE

Plastic surface mounted package

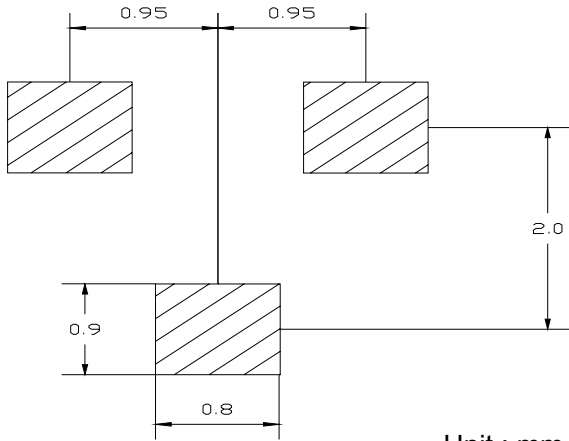
SOT-23



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SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
MMBTA05/MMBTA06	SOT-23	3000/Tape&Reel